

Roger Loo

List of Publications by Year in descending order

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445
papers

6,107
citations

126907

33
h-index

155660

55
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448
all docs

448
docs citations

448
times ranked

3664
citing authors

#	ARTICLE	IF	CITATIONS
1	GeSn/Ge heterostructure short-wave infrared photodetectors on silicon. Optics Express, 2012, 20, 27297.	3.4	169
2	Undoped and <i>in-situ</i> B doped GeSn epitaxial growth on Ge by atmospheric pressure-chemical vapor deposition. Applied Physics Letters, 2011, 99, .	3.3	168
3	Germanium-on-Silicon Mid-Infrared Arrayed Waveguide Grating Multiplexers. IEEE Photonics Technology Letters, 2013, 25, 1805-1808.	2.5	127
4	Fabrication and Analysis of a $\text{Si}_{0.55}\text{Ge}_{0.45}$ Heterojunction Line Tunnel FET. IEEE Transactions on Electron Devices, 2014, 61, 707-715.	3.0	123
5	Analysis of trap-assisted tunneling in vertical Si homo-junction and SiGe hetero-junction Tunnel-FETs. Solid-State Electronics, 2013, 83, 50-55.	1.4	117
6	Silicon-Based Photonic Integration Beyond the Telecommunication Wavelength Range. IEEE Journal of Selected Topics in Quantum Electronics, 2014, 20, 394-404.	2.9	106
7	Characterization of GeSn materials for future Ge pMOSFETs source/drain stressors. Microelectronic Engineering, 2011, 88, 342-346.	2.4	103
8	Crystalline Properties and Strain Relaxation Mechanism of CVD Grown GeSn. ECS Journal of Solid State Science and Technology, 2013, 2, P134-P137.	1.8	102
9	Site Selective Integration of III-V Materials on Si for Nanoscale Logic and Photonic Devices. Crystal Growth and Design, 2012, 12, 4696-4702.	3.0	100
10	Ge-on-Si and Ge-on-SOI thermo-optic phase shifters for the mid-infrared. Optics Express, 2014, 22, 28479.	3.4	100
11	High Quality Ge Virtual Substrates on Si Wafers with Standard STI Patterning. Journal of the Electrochemical Society, 2010, 157, H13.	2.9	83
12	A model of threading dislocation density in strain-relaxed Ge and GaAs epitaxial films on Si (100). Applied Physics Letters, 2009, 94, .	3.3	81
13	Low-temperature Ge and GeSn Chemical Vapor Deposition using Ge ₂ H ₆ . Thin Solid Films, 2012, 520, 3211-3215.	1.8	80
14	Challenges and opportunities in advanced Ge pMOSFETs. Materials Science in Semiconductor Processing, 2012, 15, 588-600.	4.0	72
15	Germanium-on-silicon planar concave grating wavelength (de)multiplexers in the mid-infrared. Applied Physics Letters, 2013, 103, .	3.3	66
16	Silicon-based heterogeneous photonic integrated circuits for the mid-infrared. Optical Materials Express, 2013, 3, 1523.	3.0	65
17	Porous silicon as an intermediate layer for thin-film solar cell. Solar Energy Materials and Solar Cells, 2001, 65, 477-485.	6.2	52
18	Thin epitaxial Si films as a passivation method for Ge(100): Influence of deposition temperature on Ge surface segregation and the high- <i>k</i> /Ge interface quality. Materials Science in Semiconductor Processing, 2006, 9, 679-684.	4.0	52

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19	A new complementary hetero-junction vertical Tunnel-FET integration scheme. , 2013, , .		50
20	Selective area growth of high quality InP on Si (001) substrates. Applied Physics Letters, 2010, 97, .	3.3	49
21	Germanium for advanced CMOS anno 2009: a SWOT analysis. , 2009, , .		48
22	Vertical ordering of islands in Ge-Si multilayers. Applied Physics A: Materials Science and Processing, 1996, 62, 575-579.	2.3	47
23	First Demonstration of Vertically Stacked Gate-All-Around Highly Strained Germanium Nanowire pFETs. IEEE Transactions on Electron Devices, 2018, 65, 5145-5150.	3.0	46
24	Characterization of Epitaxial Si:C:P and Si:P Layers for Source/Drain Formation in Advanced Bulk FinFETs. ECS Transactions, 2014, 64, 977-987.	0.5	45
25	Strained Germanium Gate-All-Around pMOS Device Demonstration Using Selective Wire Release Etch Prior to Replacement Metal Gate Deposition. IEEE Transactions on Electron Devices, 2017, 64, 4587-4593.	3.0	45
26	Advancing CMOS beyond the Si roadmap with Ge and III/V devices. , 2011, , .		43
27	Record I_{ON}/I_{OFF} performance for 65nm Ge pMOSFET and novel Si passivation scheme for improved EOT scalability. , 2008, , .		41
28	The Influence of the Epitaxial Growth Process Parameters on Layer Characteristics and Device Performance in Si-Passivated Ge pMOSFETs. Journal of the Electrochemical Society, 2009, 156, H979.	2.9	41
29	Contact resistivity and Fermi-level pinning in n-type Ge contacts with epitaxial Si-passivation. Applied Physics Letters, 2011, 98, .	3.3	40
30	(Invited) Selective Epitaxial Growth of High-P Si:P for Source/Drain Formation in Advanced Si nFETs. ECS Transactions, 2016, 75, 347-359.	0.5	37
31	Tensely strained silicon on SiGe produced by strain transfer. Applied Physics Letters, 2004, 85, 2499-2501.	3.3	36
32	Avoiding loading effects and facet growth. Applied Surface Science, 2004, 224, 24-30.	6.1	36
33	Ge-Source Vertical Tunnel FETs Using a Novel Replacement-Source Integration Scheme. IEEE Transactions on Electron Devices, 2014, 61, 4032-4039.	3.0	36
34	Fundamentals of Ge $1-x$ Sn x and Si y Ge $1-x-y$ Sn x RPCVD epitaxy. Materials Science in Semiconductor Processing, 2017, 70, 38-43.	4.0	36
35	Processing aspects in the low-frequency noise of nMOSFETs on strained-silicon substrates. IEEE Transactions on Electron Devices, 2006, 53, 1039-1047.	3.0	35
36	Successful Selective Epitaxial Si _{1-x} Ge _x Deposition Process for HBT-BiCMOS and High Mobility Heterojunction pMOS Applications. Journal of the Electrochemical Society, 2003, 150, G638.	2.9	33

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37	Low temperature Si homo-epitaxy by reduced pressure chemical vapor deposition using dichlorosilane, silane and trisilane. Journal of Crystal Growth, 2010, 312, 2671-2676.	1.5	33
38	Ge _{1-x} Sn stressors for strained-Ge CMOS. Solid-State Electronics, 2011, 60, 53-57.	1.4	33
39	Molecular beam deposition of Al ₂ O ₃ on p-Ge(001)/Ge _{0.95} Sn _{0.05} heterostructure and impact of a Ge-cap interfacial layer. Applied Physics Letters, 2011, 98, .	3.3	33
40	A new technique to fabricate ultra-shallow-junctions, combining in situ vapour HCl etching and in situ doped epitaxial SiGe re-growth. Applied Surface Science, 2004, 224, 63-67.	6.1	31
41	Reduced self-heating by strained silicon substrate engineering. Applied Surface Science, 2008, 254, 6182-6185.	6.1	31
42	High quality Ge epitaxial layers in narrow channels on Si (001) substrates. Applied Physics Letters, 2010, 96, .	3.3	31
43	Selective epitaxial deposition of strained silicon: a simple and effective method for fabricating high performance MOSFET devices. Solid-State Electronics, 2004, 48, 1307-1316.	1.4	30
44	Influence of dislocations in strained Si _{1-x} Ge _x relaxed SiGe layers on n ⁺ -p-junctions in a metal-oxide-semiconductor field-effect transistor technology. Applied Physics Letters, 2005, 87, 1921-1922.	3.3	30
45	High-Hole-Mobility Silicon Germanium on Insulator Substrates with High Crystalline Quality Obtained by the Germanium Condensation Technique. Journal of the Electrochemical Society, 2009, 156, H208.	2.9	30
46	Superior NBTI reliability of SiGe channel pMOSFETs: Replacement gate, FinFETs, and impact of Body Bias. , 2011, , .		30
47	Smooth and high quality epitaxial strained Ge grown on SiGe strain relaxed buffers with 70%–85% Ge. Journal of Crystal Growth, 2011, 324, 15-21.	1.5	30
48	Strained Germanium quantum well pMOS FinFETs fabricated on in situ phosphorus-doped SiGe strain relaxed buffer layers using a replacement Fin process. , 2013, , .		30
49	Ultimate nano-electronics: New materials and device concepts for scaling nano-electronics beyond the Si roadmap. Microelectronic Engineering, 2015, 132, 218-225.	2.4	30
50	Processing Technologies for Advanced Ge Devices. ECS Journal of Solid State Science and Technology, 2017, 6, P14-P20.	1.8	30
51	Color-sensitive photodetector based on porous silicon superlattices. Thin Solid Films, 1997, 297, 241-244.	1.8	29
52	Benefits and side effects of high temperature anneal used to reduce threading dislocation defects in epitaxial Ge layers on Si substrates. Thin Solid Films, 2008, 517, 172-177.	1.8	29
53	Strain Enhanced nMOS Using <i>In Situ</i> Doped Embedded $\text{Si}_{1-x}\text{C}_x$ S/D Stressors With up to 1.5% Substitutional Carbon Content Grown Using a Novel Deposition Process. IEEE Electron Device Letters, 2008, 29, 1206-1208.	3.9	29
54	Formation of Ni(Ge _{1-x} Sn _x) layers with solid-phase reaction in Ni/Ge _{1-x} Sn _x /Ge systems. Solid-State Electronics, 2011, 60, 46-52.	1.4	29

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55	Ge _{1-x} Sn _x Materials: Challenges and Applications. ECS Journal of Solid State Science and Technology, 2013, 2, N35-N40.	1.8	29
56	Development of a new type of SiGe thin strain relaxed buffer based on the incorporation of a carbon-containing layer. Applied Surface Science, 2004, 224, 91-94.	6.1	28
57	Improved thermal stability of Ni-silicides on Si:C epitaxial layers. Microelectronic Engineering, 2007, 84, 2542-2546.	2.4	28
58	Selective Epitaxial Growth of Germanium on Si Wafers with Shallow Trench Isolation: An Approach for Ge Virtual Substrates. ECS Transactions, 2008, 16, 829-836.	0.5	28
59	Selective Area Growth of InP in Shallow-Trench-Isolated Structures on Off-Axis Si(001) Substrates. Journal of the Electrochemical Society, 2010, 157, H1023.	2.9	28
60	Stress simulations for optimal mobility group IV p- and nMOS FinFETs for the 14 nm node and beyond. , 2012, , .		28
61	High 5.2 peak-to-valley current ratio in Si/SiGe resonant interband tunnel diodes grown by chemical vapor deposition. Applied Physics Letters, 2012, 100, .	3.3	28
62	Strained germanium quantum well p-FinFETs fabricated on 45nm Fin pitch using replacement channel, replacement metal gate and germanide-free local interconnect. , 2015, , .		28
63	25% drive current improvement for p-type multiple gate FET (MuGFET) devices by the introduction of recessed Si _{0.8} /Ge _{0.2} in the source and drain regions. , 0, , .		27
64	Investigation of plasma hydrogenation and trapping mechanism for layer transfer. Applied Physics Letters, 2005, 86, 031904.	3.3	27
65	High Ge content SGOI substrates obtained by the Ge condensation technique: A template for growth of strained epitaxial Ge. Thin Solid Films, 2008, 517, 23-26.	1.8	27
66	SiGe SEG Growth for Buried Channels p-MOS Devices. ECS Transactions, 2009, 25, 201-210.	0.5	27
67	Si/SiGe Resonant Interband Tunneling Diodes Incorporating δ -Doping Layers Grown by Chemical Vapor Deposition. IEEE Electron Device Letters, 2009, 30, 1173-1175.	3.9	27
68	Fabrication, Characterization, and Analysis of Ge/GeSn Heterojunction p-Type Tunnel Transistors. IEEE Transactions on Electron Devices, 2017, 64, 4354-4362.	3.0	27
69	High quality, relaxed SiGe epitaxial layers for solar cell application. Thin Solid Films, 1999, 337, 85-89.	1.8	26
70	Asymmetric strain relaxation in patterned SiGe layers: A means to enhance carrier mobilities in Si cap layers. Applied Physics Letters, 2007, 90, 032108.	3.3	25
71	Selective Area Growth of InP on On-Axis Si(001) Substrates with Low Antiphase Boundary Formation. Journal of the Electrochemical Society, 2012, 159, H260-H265.	2.9	25
72	Selectively grown vertical Si-p MOS transistor with short channel lengths. Electronics Letters, 1996, 32, 406.	1.0	25

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73	The vertical heterojunction MOSFET. <i>Thin Solid Films</i> , 1998, 336, 299-305.	1.8	24
74	Accurate Sheet Resistance Measurement on Ultra-Shallow Profiles. <i>Materials Research Society Symposia Proceedings</i> , 2006, 912, 1.	0.1	24
75	Si passivation for Ge pMOSFETs: Impact of Si cap growth conditions. <i>Solid-State Electronics</i> , 2011, 60, 116-121.	1.4	24
76	Ge nFET with high electron mobility and superior PBTI reliability enabled by monolayer-Si surface passivation and La-induced interface dipole formation. , 2015, , .		24
77	Extended X-ray absorption fine structure investigation of Sn local environment in strained and relaxed epitaxial Ge _{1-x} Sn _x films. <i>Journal of Applied Physics</i> , 2015, 117, .	2.5	24
78	Use of high order precursors for manufacturing gate all around devices. <i>Materials Science in Semiconductor Processing</i> , 2017, 70, 24-29.	4.0	24
79	Growth of strained Si on He ion implanted Si/SiGe heterostructures. <i>Solid-State Electronics</i> , 2006, 50, 32-37.	1.4	23
80	Density and Capture Cross-Section of Interface Traps in GeSnO ₂ and GeO ₂ Grown on Heteroepitaxial GeSn. <i>ACS Applied Materials & Interfaces</i> , 2016, 8, 13181-13186.	8.0	23
81	Compressively strained SiGe band-to-band tunneling model calibration based on p-i-n diodes and prospect of strained SiGe tunneling field-effect transistors. <i>Journal of Applied Physics</i> , 2014, 116, 214506.	2.5	22
82	Non-destructive characterization of extended crystalline defects in confined semiconductor device structures. <i>Nanoscale</i> , 2018, 10, 7058-7066.	5.6	22
83	Transmission electron microscopy investigation of the crystallographic quality of silicon films grown epitaxially on porous silicon. <i>Journal of Crystal Growth</i> , 2000, 212, 119-127.	1.5	21
84	Selective epitaxial Si/SiGe growth for VTshift adjustment in highkpMOS devices. <i>Semiconductor Science and Technology</i> , 2007, 22, S110-S113.	2.0	21
85	Low Temperature Pre-Epi Treatment: Critical Parameters to Control Interface Contamination. <i>Solid State Phenomena</i> , 2009, 145-146, 177-180.	0.3	21
86	Fabrication of high quality Ge virtual substrates by selective epitaxial growth in shallow trench isolated Si (001) trenches. <i>Thin Solid Films</i> , 2010, 518, 2538-2541.	1.8	21
87	Selective Area Growth of InP and Defect Elimination on Si (001) Substrates. <i>Journal of the Electrochemical Society</i> , 2011, 158, H645.	2.9	21
88	Selective Growth of Strained Ge Channel on Relaxed SiGe Buffer in Shallow Trench Isolation for High Mobility Ge Planar and Fin p-FET. <i>ECS Transactions</i> , 2013, 50, 39-45.	0.5	21
89	Interplay between relaxation and Sn segregation during thermal annealing of GeSn strained layers. <i>Journal of Applied Physics</i> , 2016, 120, .	2.5	21
90	An (un)solvable problem in SIMS: B-interfacial profiling. <i>Applied Surface Science</i> , 2003, 203-204, 371-376.	6.1	20

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91	On the beneficial impact of tensile-strained silicon substrates on the low-frequency noise of n-channel metal-oxide-semiconductor transistors. Applied Physics Letters, 2005, 86, 223509.	3.3	20
92	Multi-gate devices for the 32Ånm technology node and beyond: Challenges for Selective Epitaxial Growth. Thin Solid Films, 2008, 517, 101-104.	1.8	20
93	Characterization of Threading Dislocations in Thin Germanium Layers by Defect Etching: Toward Chromium and HF-Free Solution. Journal of the Electrochemical Society, 2008, 155, H677.	2.9	20
94	Vapor Phase Doping with N-type Dopant into Silicon by Atmospheric Pressure Chemical Vapor Deposition. ECS Transactions, 2008, 16, 495-502.	0.5	20
95	Record low contact resistivity to n-type Ge for CMOS and memory applications. , 2010, , .		20
96	15nm-W<inf>FIN</inf> high-performance low-defectivity strained-germanium pFinFETs with low temperature STI-last process. , 2014, , .		20
97	(Invited) Selective Etch of Si and SiGe for Gate All-Around Device Architecture. ECS Transactions, 2015, 69, 147-152.	0.5	20
98	Epitaxial GeSn: impact of process conditions on material quality. Semiconductor Science and Technology, 2018, 33, 114010.	2.0	20
99	Structural and optical properties of Ge islands grown in an industrial chemical vapor deposition reactor. Journal of Applied Physics, 2001, 90, 2565-2574.	2.5	19
100	Formation of ternary Ni-silicide on relaxed and strained SiGe layers. Microelectronic Engineering, 2004, 76, 285-289.	2.4	19
101	On the Low-Frequency Noise of pMOSFETs With Embedded SiGe Source/Drain and Fully Silicided Metal Gate. IEEE Electron Device Letters, 2007, 28, 987-989.	3.9	19
102	High Hole Mobility in 65 nm Strained Ge p-Channel Field Effect Transistors with HfO₂ Gate Dielectric. Japanese Journal of Applied Physics, 2011, 50, 04DC17.	1.5	19
103	(Invited) Status and Trends in Ge CMOS Technology. ECS Transactions, 2013, 54, 25-37.	0.5	19
104	Enhanced active P doping by using high order Ge precursors leading to intense photoluminescence. Thin Solid Films, 2016, 602, 56-59.	1.8	19
105	Reliable 50Gb/s silicon photonics platform for next-generation data center optical interconnects. , 2017, , .		19
106	Epitaxy solutions for Ge MOS technology. Thin Solid Films, 2006, 508, 292-296.	1.8	18
107	Valence band energy in confined Si1â”xGex (0.28<x<0.93) layers. Applied Physics Letters, 2009, 94, 172106.	3.3	18
108	Impact of Epi-Si growth temperature on Ge-pFET performance. , 2009, , .		18

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109	8Å T–inv– gate-first dual channel technology achieving low-V–t– high performance CMOS. , 2010, , .		18
110	Defect assessment and leakage control in Ge junctions. Microelectronic Engineering, 2014, 125, 33-37.	2.4	18
111	Review–Device Assessment of Electrically Active Defects in High-Mobility Materials. ECS Journal of Solid State Science and Technology, 2016, 5, P3149-P3165.	1.8	18
112	Electrical properties of extended defects in strain relaxed GeSn. Applied Physics Letters, 2018, 113, 022102.	3.3	18
113	Vertical Nanowire and Nanosheet FETs: Device Features, Novel Schemes for Improved Process Control and Enhanced Mobility, Potential for Faster – More Energy Efficient Circuits. , 2019, , .		18
114	Demonstration of recessed SiGe S/D and inserted metal gate on HfO/sub 2/ for high performance pFETs.. , 0, , .		17
115	Electronic properties of Ge dangling bond centers at Si1–xGex/SiO2 interfaces. Applied Physics Letters, 2009, 95, 222106.	3.3	17
116	Growth of high quality InP layers in STI trenches on miscut Si (001) substrates. Journal of Crystal Growth, 2011, 315, 32-36.	1.5	17
117	Editors' Choice–Epitaxial CVD Growth of Ultra-Thin Si Passivation Layers on Strained Ge Fin Structures. ECS Journal of Solid State Science and Technology, 2018, 7, P66-P72.	1.8	17
118	High-performance strained Si/SiGe pMOS devices with multiple quantum wells. IEEE Nanotechnology Magazine, 2002, 1, 190-194.	2.0	16
119	Progress in the physical modeling of carrier illumination. Journal of Vacuum Science & Technology B, 2006, 24, 1131.	1.3	16
120	Quantifying self-heating effects with scaling in globally strained Si MOSFETs. Solid-State Electronics, 2007, 51, 1473-1478.	1.4	16
121	Influence of Si precursor on Ge segregation during ultrathin Si reduced pressure chemical vapor deposition on Ge. Applied Physics Letters, 2009, 95, 262112.	3.3	16
122	Implant-Free SiGe Quantum Well pFET: A novel, highly scalable and low thermal budget device, featuring raised source/drain and high-mobility channel. , 2010, , .		16
123	High Absorption Contrast Quantum Confined Stark Effect in Ultra-Thin Ge/SiGe Quantum Well Stacks Grown on Si. IEEE Journal of Quantum Electronics, 2020, 56, 1-7.	1.9	16
124	Color-Sensitive Si-Photodiode Using Porous Silicon Interference Filters. Japanese Journal of Applied Physics, 1997, 36, L24-L26.	1.5	15
125	Drift mobilities and Hall scattering factors of holes in ultrathin Si1–xGex layers (0.3<x<0.4) grown on Si. Journal of Applied Physics, 2000, 88, 2016-2023.	2.5	15
126	Analysis of the Leakage Current Origin in Thin Strain Relaxed Buffer Substrates. Journal of the Electrochemical Society, 2006, 153, G379.	2.9	15

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127	Ge instability and the growth of Ge epitaxial layers in nanochannels on patterned Si (001) substrates. Journal of Applied Physics, 2010, 108, 123517.	2.5	15
128	Germanium-on-silicon mid-infrared waveguides and Mach-Zehnder interferometers. , 2013, , .		15
129	First demonstration of 15nm-W<inf>FIN</inf> inversion-mode relaxed-Germanium n-FinFETs with Si-cap free RMG and NiSiGe Source/Drain. , 2014, , .		15
130	On the manifestation of phosphorus-vacancy complexes in epitaxial Si:P films. Applied Physics Letters, 2016, 108, .	3.3	15
131	A 2nd Generation of 14/16nm-node compatible strained-Ge pFINFET with improved performance with respect to advanced Si-channel FinFETs. , 2016, , .		15
132	Properties and growth peculiarities of Si _{0.30} Ge _{0.70} stressor integrated in 14nm fin-based p-type metal-oxide-semiconductor field-effect transistors. Thin Solid Films, 2016, 602, 72-77.	1.8	15
133	Very Low Temperature Epitaxy of Group-IV Semiconductors for Use in FinFET, Stacked Nanowires and Monolithic 3D Integration. ECS Journal of Solid State Science and Technology, 2019, 8, P392-P399.	1.8	15
134	High performance Si/SiGe pMOSFETs fabricated in a standard CMOS process technology. Solid-State Electronics, 2003, 47, 1173-1177.	1.4	14
135	Defect-Free Si Thinning by In Situ HCl Vapour Etching. Solid State Phenomena, 2003, 92, 199-202.	0.3	14
136	Accurate electrical activation characterization of CMOS ultra-shallow profiles. Materials Science and Engineering B: Solid-State Materials for Advanced Technology, 2004, 114-115, 166-173.	3.5	14
137	Low-frequency noise assessment of the silicon passivation of Ge pMOSFETs. Thin Solid Films, 2010, 518, 2493-2496.	1.8	14
138	In-situ Ga doping of fully strained Ge _{1-x} Sn _x heteroepitaxial layers grown on Ge(001) substrates. Thin Solid Films, 2012, 520, 3206-3210.	1.8	14
139	Advantage of NW structure in preservation of SRB-induced strain and investigation of off-state leakage in strained stacked Ge NW pFET. , 2018, , .		14
140	50Gb/s C-band GeSi Waveguide Electro-Absorption Modulator. , 2016, , .		14
141	Photoluminescence and microstructure of self-ordered grown SiGe/Si quantum wires. Applied Physics Letters, 1995, 67, 1888-1890.	3.3	13
142	Strain relaxation of pseudomorphic Si _{1-x} Ge _x -Si(100) heterostructures after Si ⁺ ion implantation. Journal of Applied Physics, 2004, 96, 1745-1747.	2.5	13
143	Doubling or quadrupling MuGFET fin integration scheme with higher pattern fidelity, lower CD variation and higher layout efficiency. , 2006, , .		13
144	Stress Hybridization for Multigate Devices Fabricated on Supercritical Strained-SOI (SC-SSOI). IEEE Electron Device Letters, 2007, 28, 646-648.	3.9	13

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145	Germanium content dependence of the leakage current of recessed SiGe source/drain junctions. Journal of Materials Science: Materials in Electronics, 2007, 18, 787-791.	2.2	13
146	The Influence of the Epitaxial Growth Process Parameters on Layer Characteristics and Device Performance in Si-passivated Ge pMOSFETs. ECS Transactions, 2009, 19, 183-194.	0.5	13
147	Defects, Junction Leakage and Electrical Performance of Ge pFET Devices. ECS Transactions, 2009, 19, 195-205.	0.5	13
148	Use of p- and n-type vapor phase doping and sub-melt laser anneal for extension junctions in sub-32 nm CMOS technology. Thin Solid Films, 2010, 518, S48-S52.	1.8	13
149	Selective Epitaxial Growth of InP in STI Trenches on Off-Axis Si (001) Substrates. ECS Transactions, 2010, 27, 959-964.	0.5	13
150	(Invited) Assessment of Ge _{1-x} Sn _x Alloys for Strained Ge CMOS Devices. ECS Transactions, 2010, 33, 529-535.	0.5	13
151	On the interplay between relaxation, defect formation, and atomic Sn distribution in Ge(1-x)Sn(x) unraveled with atom probe tomography. Journal of Applied Physics, 2015, 118, .	2.5	13
152	Si-passivated Ge nMOS gate stack with low Dit and dipole-induced superior PBTI reliability using 3D-compatible ALD caps and high-pressure anneal. , 2016, , .		13
153	Performance and electrostatic improvement by high-pressure anneal on Si-passivated strained Ge pFinFET and gate all around devices with superior NBTI reliability. , 2017, , .		13
154	Evolution of phosphorus-vacancy clusters in epitaxial germanium. Journal of Applied Physics, 2019, 125, .	2.5	13
155	Magnetotransport and photoluminescence of two-dimensional hole gases in Si/Si _{1-x} Ge _x /Si heterostructures. Physical Review B, 1994, 50, 18113-18123.	3.2	12
156	Defect analysis of strained silicon on thin strain-relaxed buffer layers for high mobility transistors. Journal of Physics Condensed Matter, 2005, 17, S2197-S2210.	1.8	12
157	Characteristics of selective epitaxial SiGe deposition processes for recessed source/drain applications. Thin Solid Films, 2006, 508, 266-269.	1.8	12
158	Si + ion implantation for strain relaxation of pseudomorphic Si _{1-x} Ge _x /Si(100) heterostructures. Journal of Applied Physics, 2009, 105, .	2.5	12
159	Si _{1-x} Ge _x growth using Si ₃ H ₈ by low temperature chemical vapor deposition. Thin Solid Films, 2010, 518, S18-S22.	1.8	12
160	High-mobility 0.85nm-EOT Si _{0.45} Ge _{0.55} -pFETs: Delivering high performance at scaled VDD. , 2010, , .		12
161	Extended-Defect Aspects of Ge-on-Si Materials and Devices. Journal of the Electrochemical Society, 2010, 157, R1.	2.9	12
162	Analysis of Selectively Grown Epitaxial Si _{1-x} Ge _x by Spectroscopic Ellipsometry and Comparison with Other Established Techniques. Journal of the Electrochemical Society, 2000, 147, 751.	2.9	11

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163	Measurement and simulation of boron diffusion in strained Si/sub 1-x/Ge/sub x/ epitaxial layers. IEEE Transactions on Electron Devices, 2001, 48, 2022-2031.	3.0	11
164	Direct observation by resonant tunneling of the B ⁺ level in a ⁺ -doped silicon barrier. Physical Review B, 2004, 69, .	3.2	11
165	Formation of misfit dislocations at the thin strained Si ⁺ -strain-relaxed buffer interface. Applied Physics Letters, 2005, 87, 182108.	3.3	11
166	A Novel Fully Self-Aligned SiGe:C HBT Architecture Featuring a Single-Step Epitaxial Collector-Base Process. , 2007, , .		11
167	Epitaxial Ge on Standard STI Patterned Si Wafers: High Quality Virtual Substrates for Ge pMOS and III/V nMOS. ECS Transactions, 2009, 25, 335-350.	0.5	11
168	SiCP Selective Epitaxial Growth in Recessed Source/Drain Regions yielding to Drive Current Enhancement in n-channel MOSFET. ECS Transactions, 2008, 16, 1001-1013.	0.5	11
169	P+/n junction leakage in thin selectively grown Ge-in-STI substrates. Thin Solid Films, 2010, 518, 2489-2492.	1.8	11
170	Layout Scaling of $\text{Si}_{1-x}\text{Ge}_x$ Channel pFETs. IEEE Transactions on Electron Devices, 2011, 58, 2544-2550.	3.0	11
171	Boron Delta-Doping Dependence on Si/SiGe Resonant Interband Tunneling Diodes Grown by Chemical Vapor Deposition. IEEE Transactions on Electron Devices, 2012, 59, 602-609.	3.0	11
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